

Method for obtaining single-crystal scintillator on the basis of para-terphenyl is carried out by producing material in ampoule via zone melting at a rate of 10-20 mm/h and growing single crystal in growth furnace at a rate of 0.5-1.0 mm/h at a temperature of 220-230 °C. Then, ampoule is opened, and the upper and lower polycrystalline portions of obtained ingot are separated, after which single crystal is obtained.